

MIXED-MODE PROCESS

Abstract

A mixed-mode process comprises to provide a substrate first. A surface of the substrate comprises at least a first conductor in a first conductive region, at least a second conductor in a second conductive region, at least a metal-oxide-semiconductor (MOS) transistor in a MOS transistor region, and at least a capacitor in a capacitor region. A mask is then formed on the substrate to expose the second conductor. A first etching process is thereafter performed to remove a specific thickness of the second conductor followed by a first ion implantation process to dope the second conductor with first type dopants.